

L Number	Hits	Search Text	B	Time stamp
-	319	"electrically isolated electrode"	USPAT; US-PGPUB	2002/08/21 08:19
-	423	(etch\$3 near3 backside) and conduct\$3 and insulat\$3	USPAT; US-PGPUB	2002/08/22 09:22
-	51	(etch\$3 near3 backside) and conduct\$3 and insulat\$3 and trench and sidewall	USPAT; US-PGPUB	2002/08/22 10:33
-	101	(etch\$3 near3 backside) and conduct\$3 and insulat\$3 and (trench or channel or groove or via or hole) and sidewall	USPAT; US-PGPUB	2002/08/26 14:59
-	377	(etch\$3 near3 backside) and conduct\$3 and insulat\$3 and (trench or channel or groove or via or hole)	USPAT; US-PGPUB	2002/08/23 10:56
-	197	MEMS and etch\$3 and SOI	USPAT; US-PGPUB	2002/08/23 07:57
-	743	MEMS and etch\$3 and conduct\$3 and insulat\$3 and (trench or groove or via or hole or channel)	USPAT; US-PGPUB	2002/08/26 14:57
-	3709	isolated near3 (electrode or conduct\$3) and etch\$3	USPAT; US-PGPUB	2002/08/23 12:33
-	775	MEMS and etch\$3 and conduct\$3 and insulat\$3 and (trench or cavity or groove or via or hole or channel)	USPAT; US-PGPUB	2002/08/23 14:51
-	8	(silicon adj "110") same trench and etch	USPAT; US-PGPUB	2002/08/26 09:53
-	6229	etch\$3 and conduct\$3 and insulat\$3 and (trench or channel or groove or via or hole or cavity)	JPO; DERWENT	2002/08/26 15:08
-	1	etch\$3 and conduct\$3 and insulat\$3 and (trench or channel or groove or via or hole or cavity) and MEMS	JPO; DERWENT	2002/08/26 15:03
-	598	etch\$3 and conduct\$3 and insulat\$3 and trench	JPO; DERWENT	2002/08/27 10:43
-	12	etch\$3 and trench and (microelectromechanical or MEMS)	JPO; DERWENT	2002/08/27 10:44